

Maksim Ya Vinnichenko

List of Publications by Year in descending order

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papers

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56
all docs

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docs citations

56
times ranked

129
citing authors

#	ARTICLE	IF	CITATIONS
1	Electron heating in GaN/AlGaIn quantum well in a longitudinal electric field. Journal of Physics: Conference Series, 2022, 2227, 012011.	0.4	1
2	Effects of an External Magnetic Field on the Interband and Intraband Optical Properties of an Asymmetric Biconvex Lens-Shaped Quantum Dot. Nanomaterials, 2022, 12, 60.	4.1	6
3	Optical Performance of Two Dimensional Electron Gas and GaN:C Buffer Layers in AlGaIn/AlN/GaN Heterostructures on SiC Substrate. Applied Sciences (Switzerland), 2021, 11, 6053.	2.5	12
4	Optical access to folded transverse acoustic phonon doublet in 6H-SiC. Journal of Applied Physics, 2021, 129, 235701.	2.5	2
5	Photoconductivity and Infrared-Light Absorption in p-GaAs/AlGaAs Quantum Wells. Semiconductors, 2021, 55, 710.	0.5	0
6	Acceptor-related infrared optical absorption in GaAs/AlGaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 124, 114301.	2.7	4
7	Far-infrared spectroscopy of folded transverse acoustic phonons in 4H-SiC. Applied Physics Letters, 2020, 117, 202105.	3.3	2
8	2D electrons and 2D plasmons in AlGaIn/GaN nanostructure under highly non-equilibrium conditions. Journal of Physics: Conference Series, 2020, 1482, 012022.	0.4	0
9	Near-infrared optical absorption in GaN/AlN quantum wells grown by molecular-beam epitaxy. Journal of Physics: Conference Series, 2020, 1482, 012021.	0.4	1
10	Acceptor-related terahertz and infrared photoconductivity in p-type GaAs/AlGaAs quantum wells. Journal of Physics: Conference Series, 2020, 1482, 012025.	0.4	1
11	International Conference "Emerging Trends in Applied and Computational Physics 2019" (ETACP-2019). Journal of Physics: Conference Series, 2019, 1236, 011001.	0.4	0
12	Acceptor and band states in quantum wells in multiband model. Journal of Physics: Conference Series, 2019, 1236, 012006.	0.4	0
13	Determination of sign during phase correction of sign-variable modulation spectra of intersubband light absorption in GaAs/AlGaAs quantum wells. Journal of Physics: Conference Series, 2019, 1236, 012021.	0.4	0
14	Two-dimensional plasmons in a GaN/AlGaIn heterojunction. Journal of Physics: Conference Series, 2019, 1199, 012014.	0.4	2
15	Selective terahertz emission due to electrically excited 2D plasmons in AlGaIn/GaN heterostructure. Journal of Applied Physics, 2019, 126, .	2.5	26
16	Terahertz Emission due to Radiative Decay of Hot 2D Plasmons in AlGaIn/GaN Heterojunction. , 2019, , .		0
17	Non-equilibrium hole capture to excited acceptor states in quantum wells due to optical scattering. Journal of Physics: Conference Series, 2018, 993, 012016.	0.4	1
18	Polarization anisotropy of electroluminescence in indium antimonide. Journal of Physics: Conference Series, 2018, 993, 012001.	0.4	0

#	ARTICLE	IF	CITATIONS
19	Impurity-assisted terahertz photoluminescence in quantum wells under conditions of interband stimulated emission. Journal of Physics: Conference Series, 2018, 993, 012017.	0.4	0
20	Enhance of impurity related terahertz emission in optically pumped GaAs/AlGaAs quantum well structures. , 2018, , .		1
21	Temperature shift of intraband absorption peak in tunnel-coupled QW structure. Optical Materials, 2017, 66, 160-165.	3.6	4
22	The effect of Auger recombination on the nonequilibrium carrier recombination rate in the InGaAsSb/AlGaAsSb quantum wells. Superlattices and Microstructures, 2017, 109, 743-749.	3.1	4
23	Phase modulation of mid-infrared radiation in double-quantum-well structures under a lateral electric field. Semiconductors, 2017, 51, 363-366.	0.5	6
24	The effect of stimulated interband emission on the impurity-assisted far-infrared photoluminescence in GaAs/AlGaAs quantum wells. Superlattices and Microstructures, 2017, 112, 79-85.	3.1	16
25	Photoluminescence in InGaAsSb/AlGaAsSb quantum wells: impact of nonradiative recombination. Journal of Physics: Conference Series, 2017, 816, 012017.	0.4	3
26	Optical properties of GaN/AlGaN nanostructures in the terahertz frequency range. Journal of Physics: Conference Series, 2017, 816, 012019.	0.4	2
27	Electric field influence on mid-infrared absorption and interband photoluminescence in tunnel-coupled GaAs/AlGaAs quantum wells. Journal of Physics: Conference Series, 2017, 864, 012070.	0.4	0
28	Surface plasmon-phonon polaritons in GaAs. Journal of Physics: Conference Series, 2017, 917, 062038.	0.4	7
29	Luminescence and carrier concentration in Sb-containing narrow bandgap quantum wells under optical excitation. Journal of Physics: Conference Series, 2017, 917, 062027.	0.4	0
30	Terahertz absorption in GaN epitaxial layers under lateral electric field. Journal of Physics: Conference Series, 2016, 741, 012147.	0.4	0
31	Electric-field-induced mid-infrared birefringence of the double quantum wells. Journal of Physics: Conference Series, 2016, 741, 012124.	0.4	0
32	Plasmon phonon modes and optical resonances in <i>Al</i> -GaN. Journal of Physics: Conference Series, 2016, 690, 012005.	0.4	6
33	Intersubband light absorption in double GaAs/AlGaAs quantum wells under lateral electric field. Journal of Physics: Conference Series, 2016, 690, 012017.	0.4	2
34	Photo- and electroluminescence in strong electric fields in Sb-containing narrow gap semiconductor materials. Journal of Physics: Conference Series, 2016, 741, 012148.	0.4	0
35	Optical properties of GaAs/AlGaAs double quantum wells in lateral electric field. Journal of Physics: Conference Series, 2016, 741, 012149.	0.4	1
36	Polarization anisotropy of interband electroluminescence in narrow gap Sb-based semiconductors. , 2016, , .		0

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37	Terahertz radiation related to the electron relaxation after interband optical pumping in doped quantum wells. , 2016, , .		1
38	Impurity-assisted terahertz luminescence in quantum well nanostructures under interband photoexcitation. St Petersburg Polytechnical University Journal Physics and Mathematics, 2016, 2, 281-286.	0.3	0
39	Effect of Auger recombination on non-equilibrium charge carrier concentration in InGaAsSb/AlGaAsSb quantum wells. St Petersburg Polytechnical University Journal Physics and Mathematics, 2016, 2, 287-293.	0.3	1
40	Modulation of intersubband light absorption and interband photoluminescence in double GaAs/AlGaAs quantum wells under strong lateral electric fields. Semiconductors, 2016, 50, 1425-1430.	0.5	11
41	Effect of transverse electric field and temperature on light absorption in GaAs/AlGaAs tunnel-coupled quantum wells. Semiconductors, 2015, 49, 1425-1429.	0.5	10
42	Refraction index modulation induced with transverse electric field in double tunnel-coupled GaAs/AlGaAs quantum wells. Journal of Physics: Conference Series, 2015, 643, 012076.	0.4	0
43	Intersubband absorption modulation in the GaAs/AlGaAs double tunnel-coupled quantum wells. Journal of Physics: Conference Series, 2015, 586, 012012.	0.4	0
44	Intersubband light absorption in tunnel-coupled GaAs/AlGaAs quantum wells for electrooptic studies. Journal of Physics: Conference Series, 2014, 541, 012081.	0.4	4
45	Photoluminescence dynamics in InGaAsSb/AlGaAsSb quantum well nanostructures. Semiconductors, 2013, 47, 146-151.	0.5	3
46	Lateral photoconductivity in structures with Ge/Si quantum dots. Semiconductors, 2013, 47, 1574-1577.	0.5	13
47	Dependence of the carrier concentration on the current in mid-infrared injection lasers with quantum wells. Semiconductors, 2013, 47, 1513-1516.	0.5	4
48	Mid infrared optical properties of Ge/Si quantum dots with different doping level. , 2013, , .		0
49	Dynamics of charge carrier recombination and capture in laser nanostructures with InGaAsSb/AlGaAsSb quantum wells. , 2013, , .		0
50	Emission of terahertz radiation from selectively doped AlGaN/GaN heterostructures under the heating of two-dimensional electrons by an electric field. Bulletin of the Russian Academy of Sciences: Physics, 2012, 76, 207-210.	0.6	1
51	Influence of Auger recombination on the lifetime of nonequilibrium carriers in InGaAsSb/AlGaAsSb quantum well structures. Bulletin of the Russian Academy of Sciences: Physics, 2012, 76, 211-213.	0.6	1
52	Carrier heating in quantum wells under optical and current injection of electron-hole pairs. Semiconductors, 2010, 44, 1402-1405.	0.5	11
53	Absorption and modulation of absorption in p-GaAs/AlGaAs quantum well nanostructures. Bulletin of the Russian Academy of Sciences: Physics, 2010, 74, 82-85.	0.6	0
54	Hot charge-carrier electroluminescence from laser nanostructures in the spontaneous and stimulated emission modes and absorption of IR radiation by hot electrons in quantum wells. Bulletin of the Russian Academy of Sciences: Physics, 2009, 73, 73-76.	0.6	0

#	ARTICLE	IF	CITATIONS
55	Light absorption related to hole transitions in quantum dots and impurity centers in quantum wells under external excitation. Journal of Physics: Conference Series, 2009, 193, 012059.	0.4	1